

Sub B1

WHAT IS CLAIMED IS:

1. A semiconductor device comprising:
a cobalt including layer having oxidation resistive and
fluorinated acid resistive; and
a clad layer for cladding said cobalt including layer.
2. The semiconductor device as cited in Claim 1, wherein
said cobalt including layer comprising of the cobalt tungsten
phosphor layer.
3. The semiconductor device as cited in Claim 1, wherein
said clad layer comprising of a cobalt silicide layer.
4. The semiconductor device as cited in Claim 1, wherein
said cobalt including layer being formed on a copper wiring
face.
5. A method for manufacturing a semiconductor device
comprising the steps of:
forming a cobalt including layer; and
forming a cobalt silicide layer on said surface of the cobalt
including layer.
6. The method as cited in claim 5, wherein
said cobalt silicide layer being formed by exposing said cobalt
including layer in a silane system gas.

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7. The method as cited in claim 5, wherein
said cobalt including layer is a cobalt tungsten phosphor layer.

End B2